



UT5003

Power MOSFET

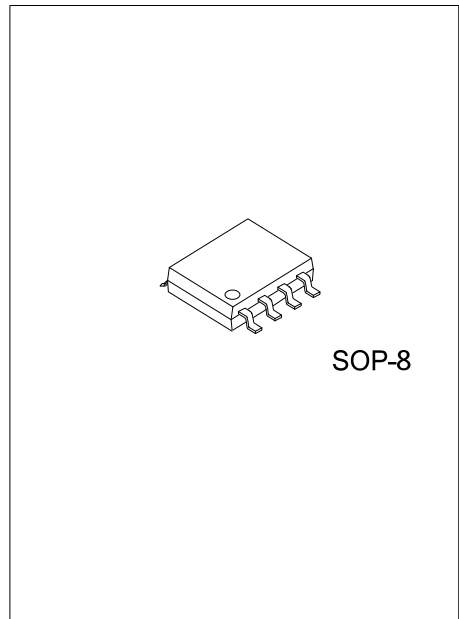
DUAL ENHANCEMENT MODE (N-CHANNEL/P-CHANNEL)

DESCRIPTION

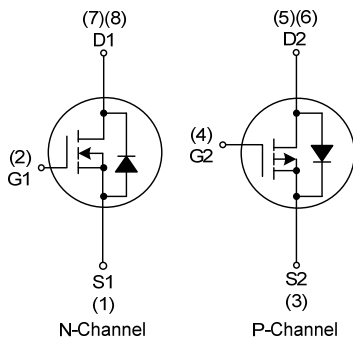
The **UT5003** can provide excellent $R_{DS(ON)}$ and low gate charge by using UTC's advanced trench technology. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * N-Channel: 30V, 7A
 $R_{DS(ON)} < 27.5m\Omega @ V_{GS}=10V, I_D=7A$
 $R_{DS(ON)} < 40m\Omega @ V_{GS}=4.5V, I_D=6A$
- * P-Channel: -30V, -5A
 $R_{DS(ON)} < 45m\Omega @ V_{GS}=-10V, I_D=-5A$
 $R_{DS(ON)} < 80m\Omega @ V_{GS}=-4.5V, I_D=-4A$
- * Super high dense cell design
- * Reliable and rugged



SYMBOL



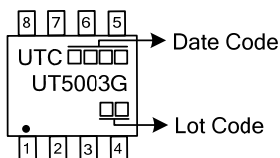
ORDERING INFORMATION

Ordering Number	Package	Pin Assignment								Packing
		1	2	3	4	5	6	7	8	
UT5003G-S08-R	SOP-8	S1	G1	S2	G2	D2	D2	D1	D1	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UT5003G-S08-R</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Green Package 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) S08: SOP-8 (3) G: Halogen Free and Lead Free
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

N-Channel:

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note3)	I_D	7	A
Pulsed Drain Current (Note3)	I_{DM}	20	A
Power Dissipation	P_D	2	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

P-Channel:

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note3)	I_D	-5	A
Pulsed Drain Current (Note3)	I_{DM}	-20	A
Power Dissipation	P_D	2	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note3)	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

N-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=24\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.5	2.5	V
Drain-Source On-State Resistance (Note2)	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=7\text{A}$		20.5	27.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=6\text{A}$		30	40	$\text{m}\Omega$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$		680		pF
Output Capacitance	C_{OSS}			105		pF
Reverse Transfer Capacitance	C_{RSS}			75		pF
SWITCHING CHARACTERISTICS						
Turn-ON Delay Time (Note2)	$t_{D(ON)}$	$V_{DS}=10\text{V}, V_{GS}=10\text{V}, I_D=1\text{A}, R_G=3\Omega$		4.6	7	ns
Turn-ON Rise Time	t_R			4	6	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20	30	ns
Turn-OFF Fall Time	t_F			5	8	ns
Total Gate Charge (Note2)	Q_G	$V_{DS}=0.5 \cdot BV_{DSS}, V_{GS}=10\text{V}, I_D=7\text{A}$		14		nC
Gate-Source Charge	Q_{GS}			1.9		nC
Gate-Drain Charge	Q_{GD}			3.3		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	$I_S=1\text{A}, V_{GS}=0\text{V}$			1	V
Diode Continuous Forward Current	I_S				1.3	A

■ ELECTRICAL CHARACTERISTICS (Cont.)

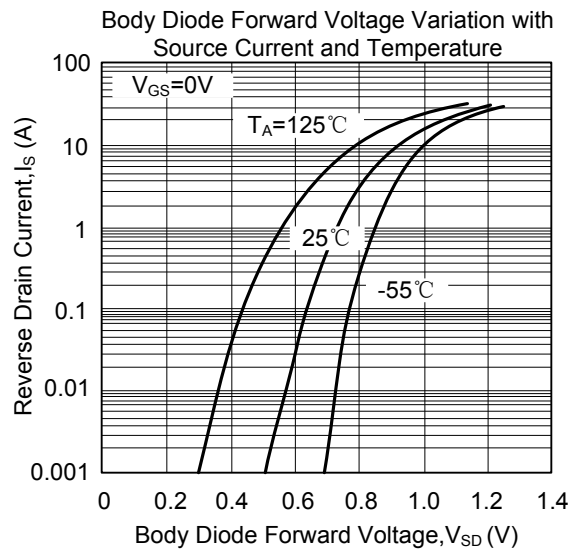
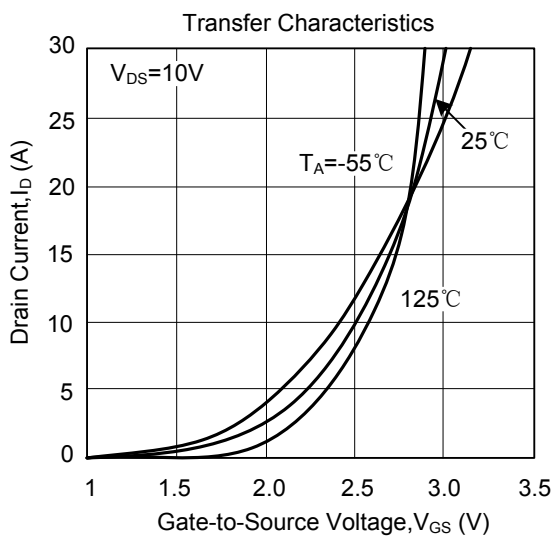
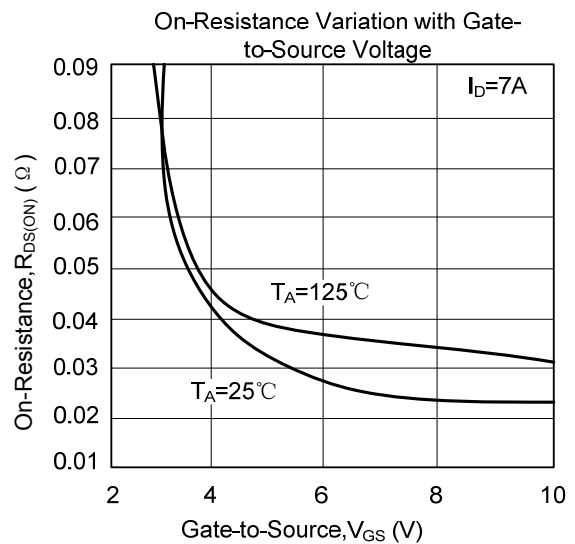
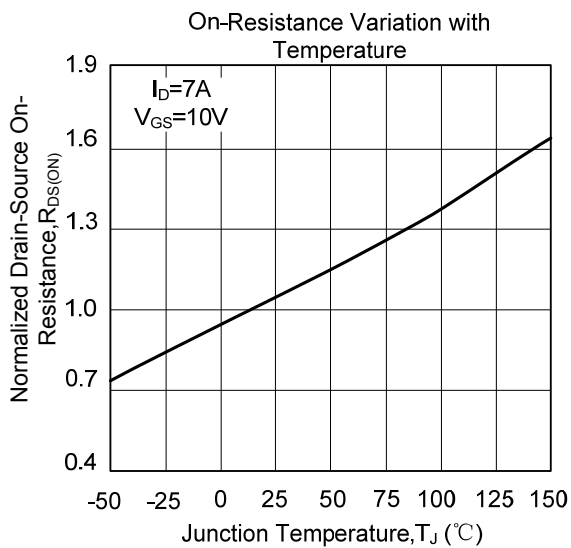
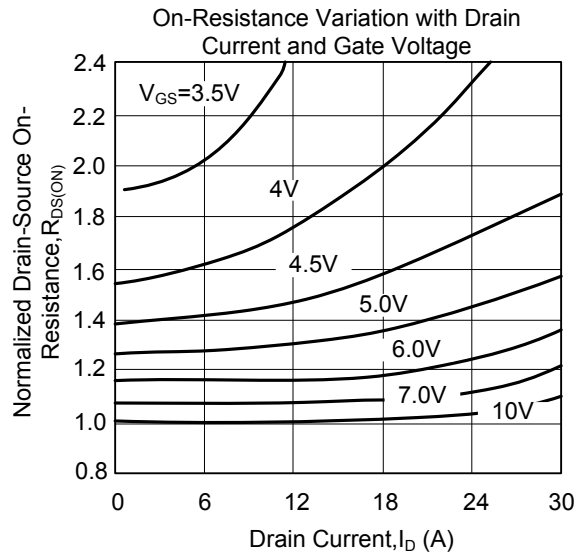
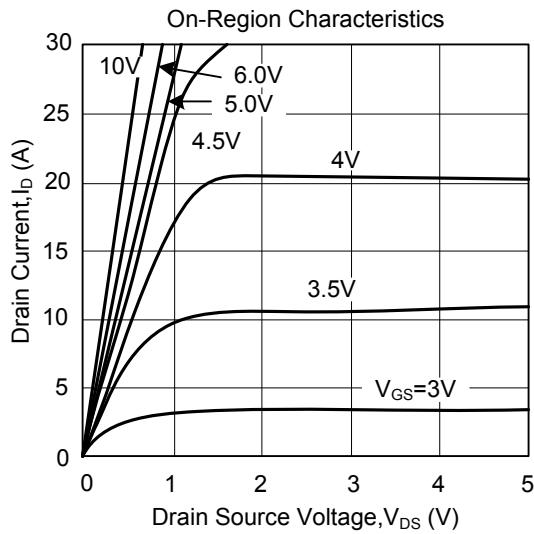
P-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-2.5	V
Drain-Source On-State Resistance (Note2)	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-5A$		37.5	45	m Ω
		$V_{GS}=-4.5V, I_D=-4A$		62	80	m Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=-15V, f=1MHz$		780		pF
Output Capacitance	C_{OSS}			145		pF
Reverse Transfer Capacitance	C_{RSS}			79		pF
SWITCHING CHARACTERISTICS						
Turn-ON Delay Time (Note2)	$t_{D(ON)}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=1A, R_G=3\Omega$		7.7	11.5	ns
Turn-ON Rise Time	t_R			5.7	8.5	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20	30	ns
Turn-OFF Fall Time	t_F			9.5	14	ns
Total Gate Charge (Note2)	Q_G	$V_{DS}=0.5 \cdot BV_{DSS}, V_{GS}=-10V, I_D=-5A$		15.1		nC
Gate-Source Charge	Q_{GS}			2.1		nC
Gate-Drain Charge	Q_{GD}			4.0		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	$I_S=-1A, V_{GS}=0V$			-1	V
Diode Continuous Forward Current	I_S				-1.3	A

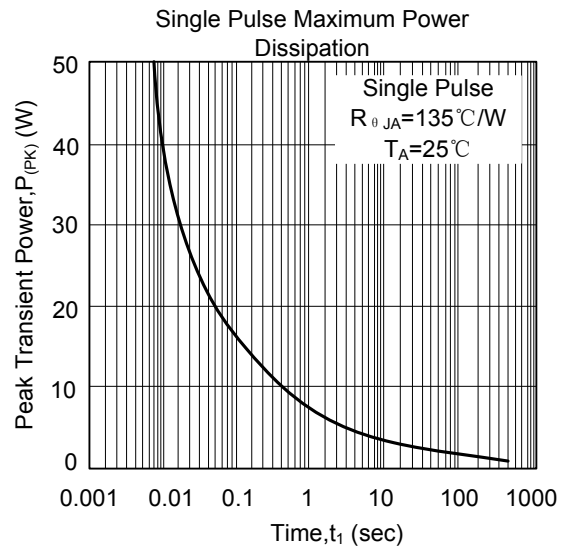
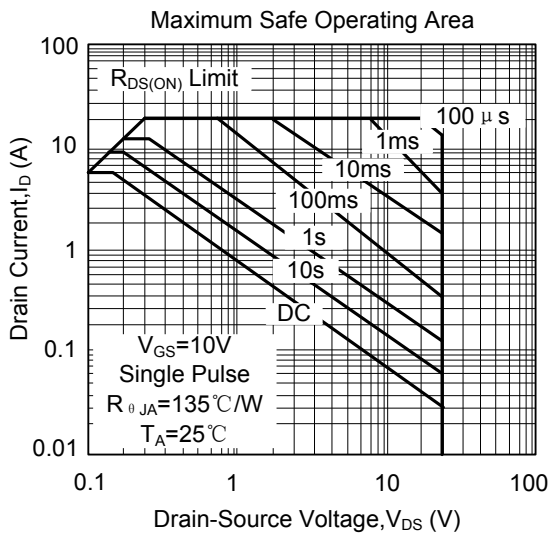
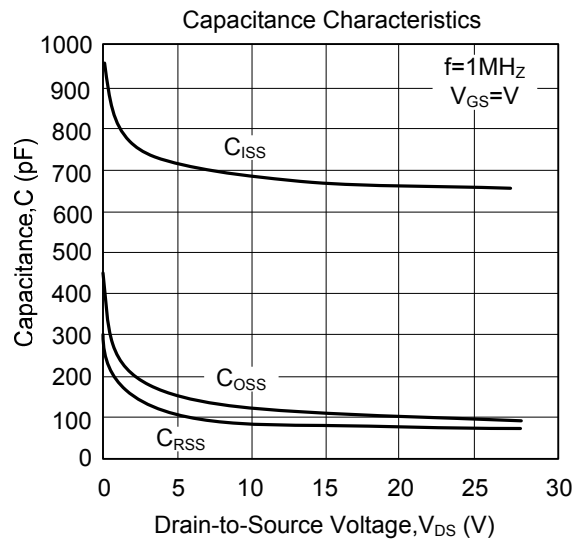
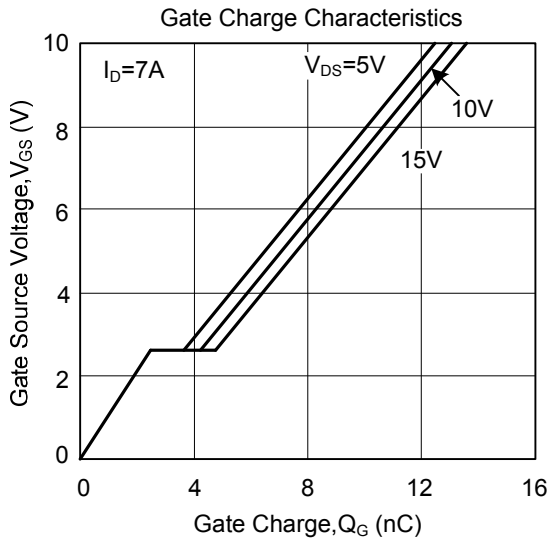
- Notes: 1. Pulse width limited by $T_{J(MAX)}$
 2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 3. Surface Mounted on $1in^2$ pad area, $t \leq 10sec$.

TYPICAL CHARACTERISTICS

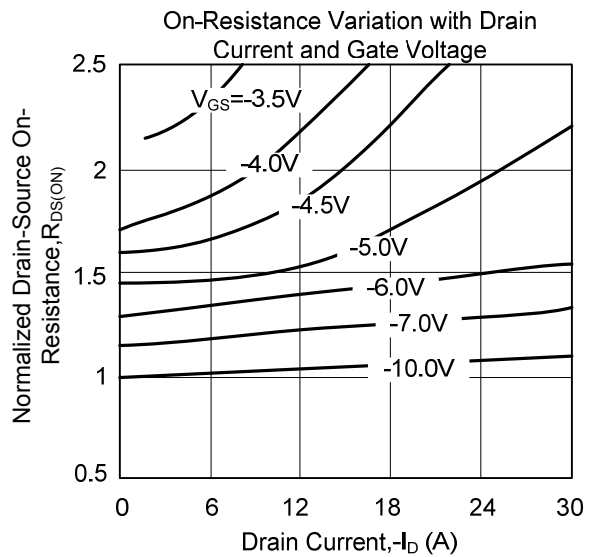
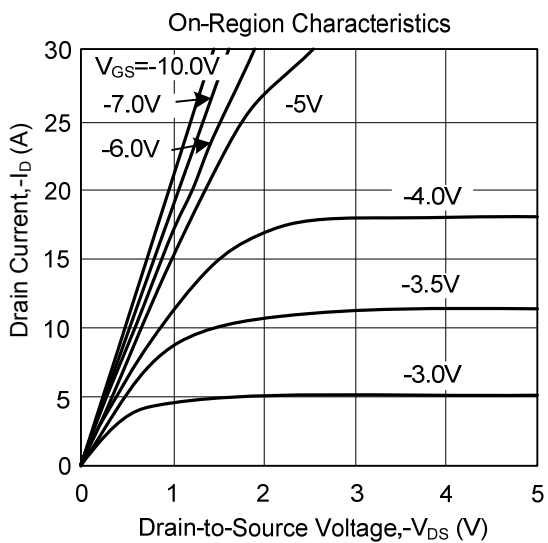
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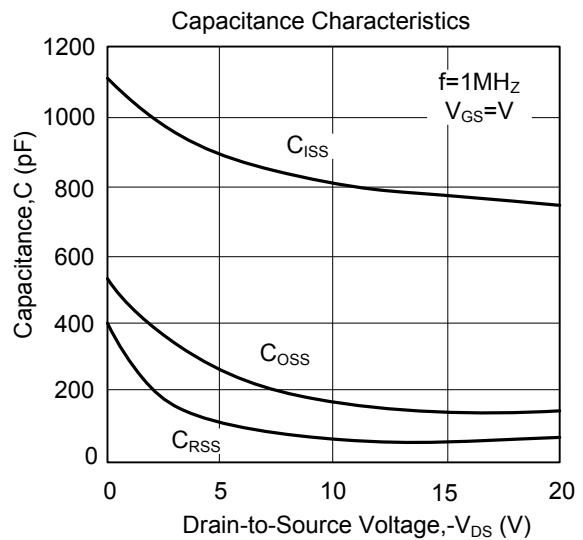
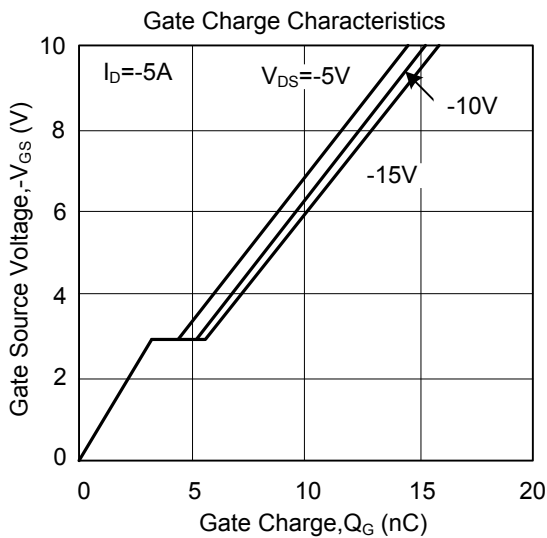
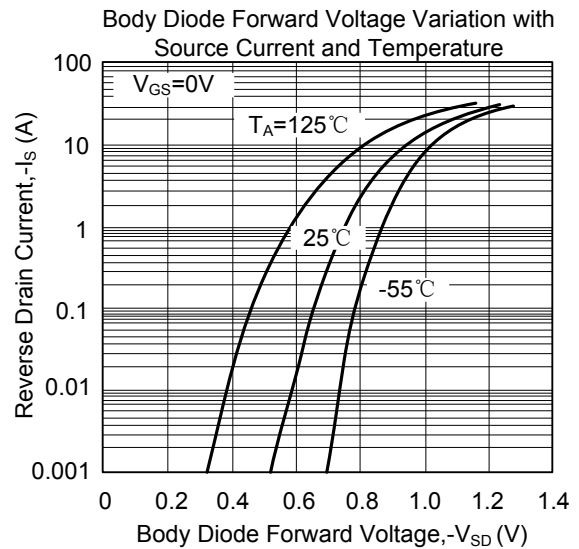
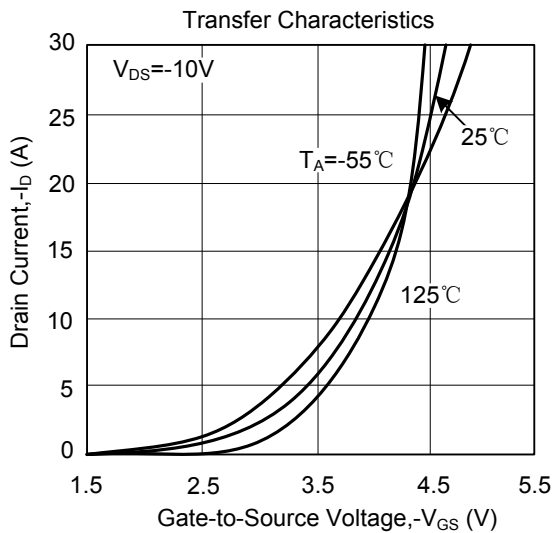
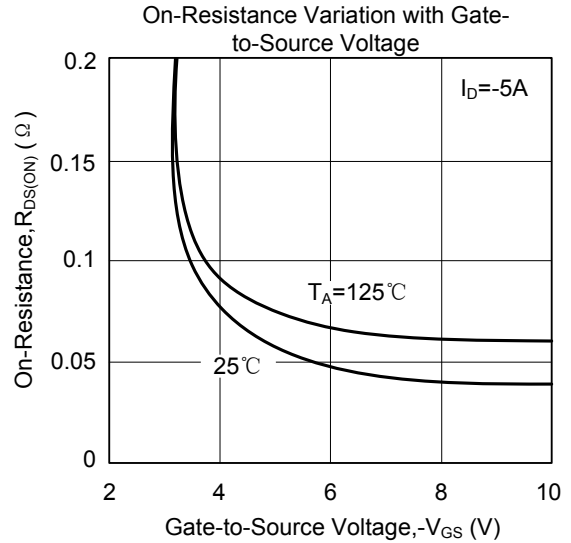
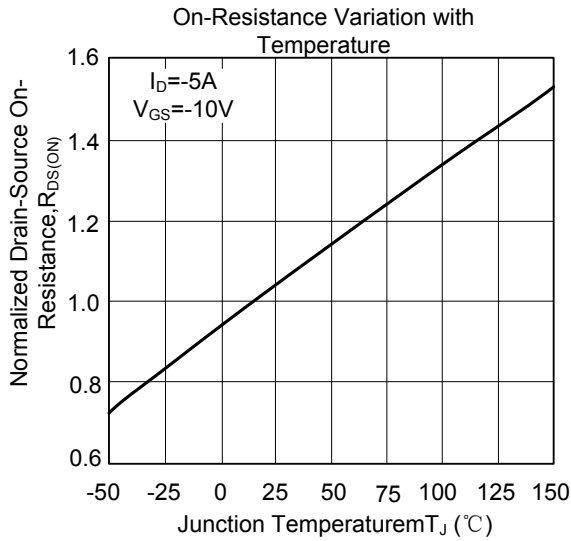
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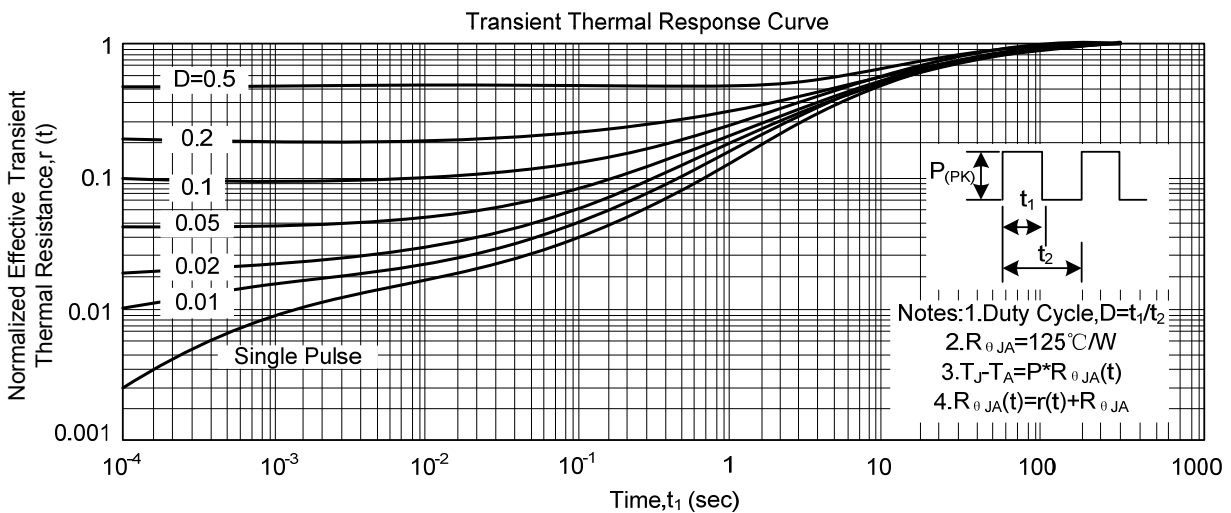
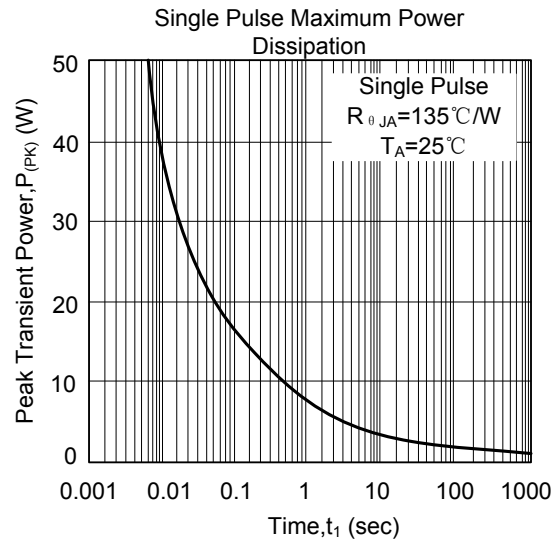
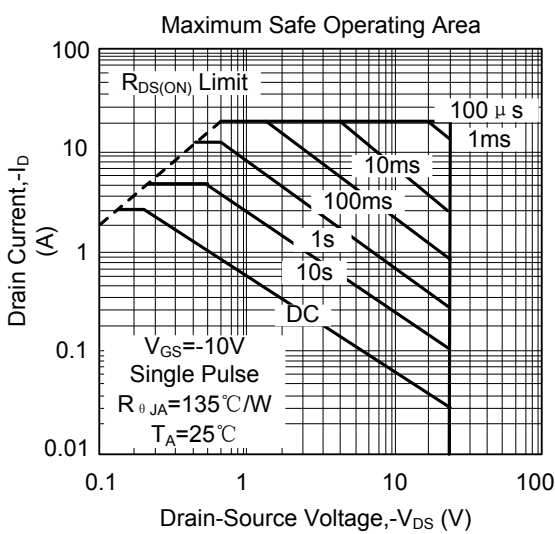
P-CHANNEL



TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)



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